# Analysis of Fused Thiophene Polymer Field Effect Transistors (FET)

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## **Polymer FET Importance**

Low cost manufacturing Low energy fabrication Low environmental impact



Versatile processing



Flexible substrates

# Field Effect Transistor (FET)

- 1. Transistors are logic switches
- 2. Controlled by a gate voltage



# **PolyFETs and Doping**







In off state

current still flows (always On!)

### Goals

Define ideal operating parameters for viable commercial devices.



#### **Experimental Methods**



### **Experimental Methods**



#### **Research Data – Dopant Effects**



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### Research Data – Bias Meas.



#### Research Data – $V_T$ Results



### Conclusions

- O<sub>2</sub> and N<sub>2</sub> device results comparable
- Minimal hysteresis for pulsed operation
- $V_T$  shift is  $V_G$  dependent normal
- Quick recovery under bias testing
- No permanent damage under bias testing

#### On-going research:

- Finish bias testing conditions
  •O<sub>2</sub> and H<sub>2</sub>O
- Look at different dielectrics
  - polystyrene, poly(methyl methacrylate)

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### **Experimental Methods**

